

Docket No. 197802US-2S

IN RE APPLICATION OF: Wakako MORIYAMA ET AL.

SERIAL NO: 09/670,520

FILED: SEPTEMBER 26, 2000

FOR: METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICES USING THERMAL NITRIDE FILMS AS GATE INSULATING FILMS



ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Transmitted herewith is an amendment in the above-identified application.

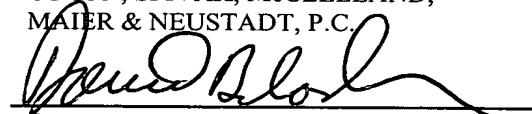
No additional fee is required
 Small entity status of this application under 37 C.F.R. §1.9 and §1.27 is claimed.
 Additional documents filed herewith: Marked-up Copy of Amendment

The Fee has been calculated as shown below:

CLAIMS	CLAIMS REMAINING		HIGHEST NUMBER PREVIOUSLY PAID	NO. EXTRA CLAIMS	RATE	CALCULATIONS
TOTAL	15	MINUS	22	0	× \$18 =	\$0.00
INDEPENDENT	6	MINUS	6	0	× \$84 =	\$0.00
		<input type="checkbox"/> MULTIPLE DEPENDENT CLAIMS		+ \$280 =		\$0.00
						\$0.00
		<input type="checkbox"/> Reduction by 50% for filing by Small Entity				\$0.00
		<input type="checkbox"/> Recordation of Assignment		+ \$40 =		\$0.00
						TOTAL \$0.00

A check in the amount of _____ is attached.
 Please charge any additional Fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.
 If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time may be charged to Deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

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197802US-2S



#6 Amend a
Action
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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

WAKAKO MORIYAMA ET AL

: EXAMINER: LEE, G. D.

SERIAL NO: 09/670,520

: GROUP ART UNIT: 2825

FILED: SEPTEMBER 26, 2000
FOR: METHOD FOR MANUFACTURING
SEMICONDUCTOR DEVICES
USING THERMAL NITRIDE FILMS
AS GATE INSULATING FILMS

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action mailed April 25, 2002, please amend this application as follows:

IN THE SPECIFICATION

Please amend the specification to read as follows:¹

Please delete the BRIEF SUMMARY OF THE INVENTION in its entirety at page 6, line 2 to page 14, line 20 and substitute therefor:

According to an aspect of the present invention, there is provided a semiconductor device manufacturing method comprising forming a gate insulating film in an oxynitride form on a main surface of a semiconductor substrate; forming gate electrodes on the gate

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¹A marked-up copy of the changes made to the specification is attached.